

AO6804

Dual N-Channel Enhancement Mode Field Effect Transistor



General Description

The AO6804 uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications. AO6804 is Pb-free (meets ROHS & Sony 259 specifications).

Features

 $V_{DS} = 20V$

 $I_{D} = 5.0A$ $(V_{GS} = 4.5V)$

Typical Rds

 $R_{DS(ON)} < 24m\Omega (V_{GS} = 4.5V)$

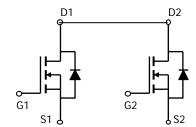
 $R_{DS(ON)}$ < 26m Ω (V_{GS} = 4.0V)

 $R_{DS(ON)}$ < 28m Ω (V_{GS} = 3.1V)

 $R_{DS(ON)} < 31m\Omega (V_{GS} = 2.5V)$

TSOP6 **Top View**

$$\begin{array}{c|cccc} S1 & \hline & 1 & 6 \\ D1/D2 & \hline & 2 & 5 \\ S2 & \hline & 3 & 4 \\ \hline \end{array} \begin{array}{c} G1 \\ D1/D2 \\ G2 \\ \end{array}$$



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	10 Sec	Steady State	Units
Drain-Source Voltage		V_{DS}	20		V
Gate-Source Voltage		V_{GS}	<u> </u>	:12	V
Continuous Drain	T _A =25°C		5	4	
Current ^A	T _A =70°C	I _D	4	3.2	Α
Pulsed Drain Current B		I _{DM}	25		
Danna Diagination A	T _A =25°C	В	1.3	0.8	W
Power Dissipation ^A	T _A =70°C	$-P_{D}$	0.8	0.5	VV
Junction and Storage	Temperature Range	T_J , T_{STG}	-55 ·	to 150	°C

Thermal Characteristics					
Parameter	Symbol	Тур	Max	Units	
Maximum Junction-to-Ambient A	t ≤ 10s	$R_{\scriptscriptstyle{ hetaJA}}$	76	95	°C/W
Maximum Junction-to-Ambient A	Steady State	IN _θ JA	118	150	°C/W
Maximum Junction-to-Lead ^C	Steady State	$R_{ hetaJL}$	54	68	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	20			V
lass	Zero Gate Voltage Drain Current	$V_{DS} = 20V, V_{GS} = 0V$			1	μА
I _{DSS}	Zero Gate Voltage Drain Current	$T_J = 55^{\circ}C$			5	μΑ
I_{GSS}	Gate-Body leakage current	$V_{DS} = 0V, V_{GS} = \pm 12V$			±500	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS} I_D = 250 \mu A$	0.5	0.75	1.2	V
$I_{D(ON)}$	On state drain current	$V_{GS} = 4.5V$, $V_{DS} = 5V$	25			Α
4411 a a ma		$V_{GS} = 4.5V, I_D = 5.0A$	18	24	32	m()
st4U.com		T _J =125°C	25	33	43	mΩ
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 4.0V, I_D = 4.5A$	22	26	34	mΩ
		$V_{GS} = 3.1V, I_D = 4.5A$	21	28	37	mΩ
		$V_{GS} = 2.5V, I_D = 4.0A$	22	31	42	mΩ
g _{FS}	Forward Transconductance	$V_{DS} = 5V, I_{D} = 5.0A$		7		S
V_{SD}	Diode Forward Voltage	$I_S = 1A, V_{GS} = 0V$		0.65	1	V
Is	Maximum Body-Diode Continuous Curre	ent			1.1	Α
DYNAMIC	PARAMETERS					
C _{iss}	Input Capacitance			580	725	pF
C _{oss}	Output Capacitance	V _{GS} =0V, V _{DS} =10V, f=1MHz		95		pF
C _{rss}	Reverse Transfer Capacitance]		70		pF
R_g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		3.5	5.3	Ω
SWITCHII	NG PARAMETERS	-				
Q_g	Total Gate Charge			5.8	7.7	nC
Q_{gs}	Gate Source Charge	V_{GS} = 4.5V, V_{DS} = 10V, I_{D} = 5A		1		nC
Q_{gd}	Gate Drain Charge	1 1		1.6		nC
t _{D(on)}	Turn-On DelayTime			2.4		ns
t _r	Turn-On Rise Time	V_{GS} =10V, V_{DS} =10V, R_L =2.0 Ω ,		6.4		ns
$t_{D(off)}$	Turn-Off DelayTime	R_{GEN} =3 Ω		38		ns
t _f	Turn-Off Fall Time]		9.5		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =5A, dI/dt=100A/μs		18	24	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I _F =5A, dI/dt=100A/μs		6		nC

A: The value of R $_{6JA}$ is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with T $_A$ = 25°C. in any given application depends on the user's specific board design. The current rating is based on the t \leq 10s thermal resistance rating. B: Repetitive rating, pulse width limited by junction temperature.

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C. The R $_{\theta JA}$ is the sum of the thermal impedence from junction to lead R $_{\theta JL}$ and lead to ambient.

D. The static characteristics in Figures 1 to 6 are obtained using < 300 μs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T $_A$ =25°C. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

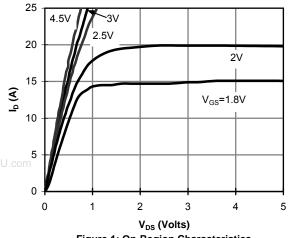


Figure 1: On-Region Characteristics

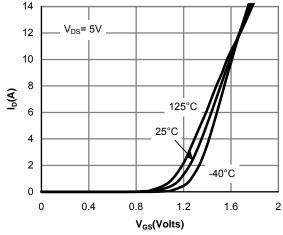


Figure 2: Transfer Characteristics

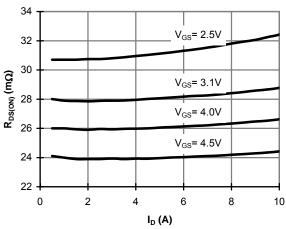


Figure 3: On-Resistance vs. Drain Current and **Gate Voltage**

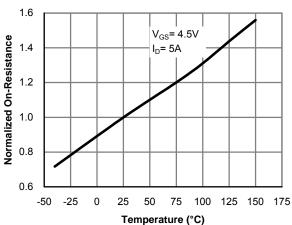


Figure 4: On-Resistance vs. Junction Temperature

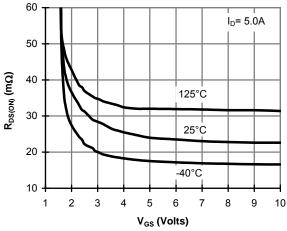


Figure 5: On-Resistance vs. Gate-Source Voltage

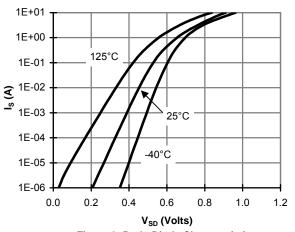
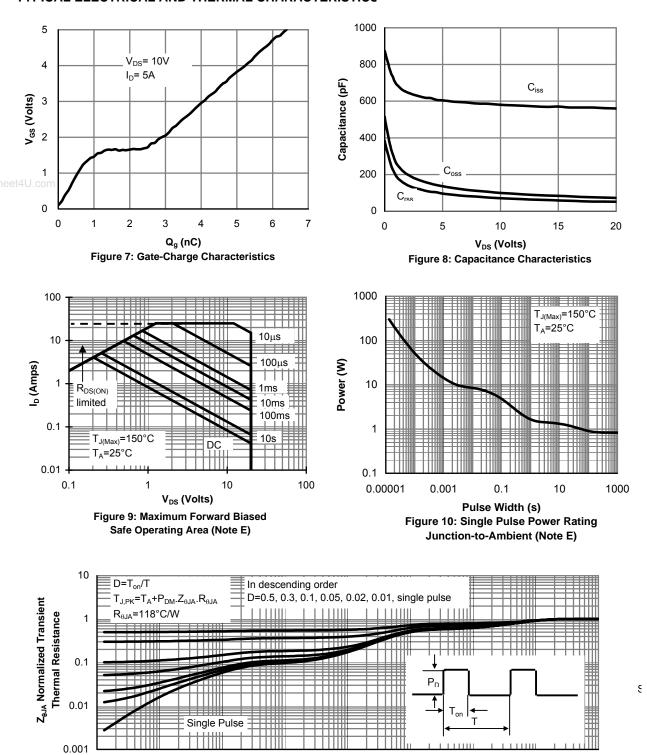


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



Pulse Width (s)
Figure 11: Normalized Maximum Transient Thermal Impedance(Note E)

0.1

10

100

1000

0.0001

0.001

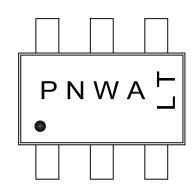
0.01

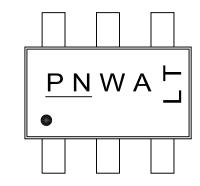
0.00001



Document No.	PD-00731		
Version	A		
Title	AO6804 Marking Description		

TSOP-6 PACKAGE MARKING DESCRIPTION





Standard product

Green product

NOTE:

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P - Package and product type

N - Last digital of product number

W - Year and week code

A - Assembly location code

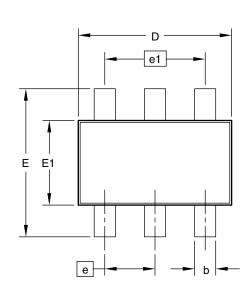
L&T - Assembly lot code

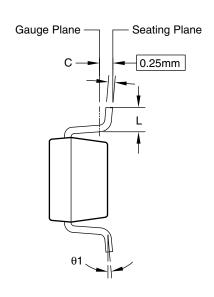
PART NO.	DESCRIPTION	CODE (PN)
AO6804	Standard product	H4
AO6804L	Green product	<u>H4</u>

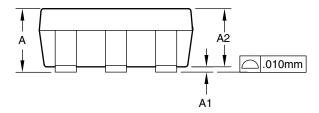


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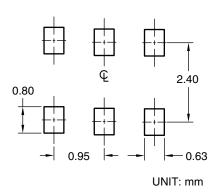
TSOP-6L Package Dimensions







RECOMMENDED LAND PATTERN



Dimensions in millimeters

Symbols	Min. Nom.		Max.	
Α	0.90	_	1.25	
A1	0.00	_	0.15	
A2	0.70	1.10	1.20	
b	0.30	0.40	0.50	
С	0.08	0.13	0.20	
D	2.70	2.90	3.10	
E	2.50	2.80	3.10	
E1	1.50	1.60	1.70	
е	0.95 BSC			
e1	1.90 BSC			
L	0.30	_	0.60	
θ1	O°	_	8°	

Dimensions in inches

Symbols	Min.	Nom.	Max.		
Α	0.035		0.049		
A1	0.00	_	0.006		
A2	0.028	0.043	0.047		
b	0.012	0.016	0.020		
С	0.003	0.005	0.008		
D	0.106	0.114	0.122		
E	0.098	0.110	0.122		
E1	0.059	0.063	0.067		
е	0.037 BSC				
e1	0.075 BSC				
L	0.012	_	0.024		
θ1	0°		8°		

Notes:

- 1. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 2. Dimension L is measured in gauge plane.
- 3. Tolerance: ±0.100mm (4 mils) unless otherwise specified.
- 4. Followed from JEDEC MO-178C & MO-193C.
- 5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

